Inverted type bulk-heterojunction organic solar cell using electrodeposited titanium oxide thin films as electron collector electrode

著者	Kuwabara Takayuki, Sugiyama Hirokazu,
	Yamaguchi Takahiro, Takahashi Koshin
journal or	Thin Solid Films
publication title	
volume	517
number	13
page range	3766-3769
year	2009-05-01
URL	http://hdl.handle.net/2297/17598

doi: 10.1016/j.tsf.2008.12.039

Inverted type bulk-heterojunction organic solar cell using electrodeposited

titanium oxide thin films as electron collector electrode

Takayuki Kuwabara*, Hirokazu Sugiyama, Takahiro Yamaguchi, Kohshin Takahashi*

Graduate School of Natural Science and Technology, Kanazawa University, Kakuma-machi,

Kanazawa, Ishikawa 920-1192, Japan

* Corresponding author: TEL: +81-76-234-4770

FAX: +81-76-234-4800

E-mail: <u>tkuwa@t.kanazawa-u.ac.jp</u>

Submitted to Thin Solid Films

1

Abstract

We developed an inverted type bulk-heterojunction organic solar cell with 1 cm² active

area using a fluorine-doped tin oxide / electrodeposited amorphous (TiO_x) or anatase (TiO₂)

titanium oxide electrode instead of the low work-functional electrode such as Al. The cell

with TiO₂ showed the power conversion efficiency (η) of 2.5 % by irradiating AM 1.5-100

 $mW\ cm^{-2}$ simulated sunlight. While, the performance of the cell with TiO_x was almost

maintained in an ambient atmosphere under continuous light irradiation of 10 h, although

slightly small initial η value of 2.1% was observed.

Key words: Organic thin film solar cells, electrodepositied titanium oxide, air-stable

2

Main Text

1. Introduction

Organic solar cells have been attracting much attention as a candidate for socially acceptable "renewable energy source" instead of the fossil fuel due to providing lower cost and environment-friendly energy conversion system. An Al metal has been often used as the anodic electrode of the organic solar cells, which are termed "normal type solar cells" as shown in Figure 1(a), because of its low work function. But there is a problem for its durability because the Al surface is easily oxidized to insulator Al₂O₃ in air. Recently, the developments of the solar cells using non-corrosive electrode instead of the Al anode have been carried out by several research groups in order to solve this problem. Their solar cells have the inverted device structure against normal type solar cells, that is, their photo-generated electrons flow through external circuit from the ITO electrode to Au electrode. Therefore they are called "inverted type solar cells" as shown in Figure 1(b). Although metals such as In [1-3] or n-type semiconductors such as TiO₂ [4-8] and ZnO [3, 9, 10] prepared by a sol-gel technique have been often used as electron collector electrodes of the inverted type solar cells, the organic thin film solar cells using an electrodeposited technique have hardly been developed. Because the fabrication of the solar cells requires the control of each layer in nanometer-scale thickness, it is not tried to apply the electrodeposited film having an unevenness surface for the solar cells. In our research, we developed the inverted type solar cells using the electrodeposited amorphous (TiO_x) and anatase titanium oxide (TiO₂) layers. Figure 1(c) shows the energy-level diagram of the inverted type solar cells. n-Type transparent semiconductor TiO_x and TiO₂ layers were expected as an electron collector because the bottom energy level of the conduction band of titanium(IV) oxide located down to the LUMO level of acceptor PCBM. Herein, we report the performance of a

fluorine-doped tin oxide (FTO)/ TiO_x or TiO_2 /regioregular poly(3-hexylthiophene) (P3HT):[6,6]-phenyl C_{61} butyric acid methyl ester (PCBM)/ poly(3,4-ethylenedioxylenethiophene):poly(4-styrene sulfonic acid) (PEDOT:PSS)/Au inverted type bulk-heterojunction organic solar cell.

2. Experiments

2.1. Materials.

Titanium(IV) oxysulfate solution (TiOSO₄, 99.99 %, ~15 wt. % in dilute sulfuric acid), titanium(IV) isopropoxide (Ti[OCH(CH₃)₂]₄, 99.999 %), 2-methoxyethanol (CH₃OCH₂CH₂OH, 99.9 %), acetyl acetone (AA; CH₃C(O)CH₂C(O)CH₃, 99 %), regioregular P3HT (Mw ~ 87,000), PEDOT-PSS 1.3 wt% dispersion in water, and chlorobenzene were purchased from Sigma-Aldrich Chemical Co., Inc. Hydrogen peroxide (H₂O₂, 30.0 ~ 35.5 %) and 2-propanol (dehydrated, 99.5 %) were purchased from Kanto Chemical Co., Inc. All the chemicals were used as received. FTO substrate (A110U80, 12 Ω / \square) was purchased from AGC Fabritech Co., Ltd.

2.2. Fabrications of organic thin film solar cells using electrodeposited titanium oxide thin films.

All the operations except the vacuum deposition and the sealing treatment were implemented in air. An FTO electrode was used as transparent conductive oxide, because its electric resistance hardly increased by heat treatment at 450 $^{\circ}$ C and it has a resistance to electrochemical reduction. The FTO electrode was ultrasonicated in 2-propanol, and then cleaned in boiling 2-propanol, and subsequently dried. The titanium oxide precursor (TiO(OH)₂ • x H₂O) film was prepared on the FTO by electrodepositing potentiostatically at -2.2 V vs Ag/AgCl in a solution containing 0.01 M TiOSO₄, 0.03 M H₂O₂, and 0.3 M KNO₃

[11, 12] and by consuming the electric charge of 400 mC cm⁻². After the as-deposited film was washed with water and dried in air, the TiO(OH)2 • x H2O was converted to the amorphous TiO_x or the crystalline TiO₂ by heat treatment at 150 or 450 °C for 1 h. The preparation of sol-gel TiO_x precursor film was based on the method described by Kim et al [13, 14]. Titanium (IV) isopropoxide (2.4 g, 8.44 mmol) was slowly added to 2-methoxyethanol (12.5 mL) cooled by an ice bath to avoid drastic temperature increase, and then the mixture solution was refluxed for 1 h. Further, the solution was cooled by the ice bath, and AA (2.07 g, 20.7 mmol) as the stabilizer was slowly added to its cooled solution, followed by refluxing for 1 h to obtain the TiO_x precursor solution. AA-TiO_x precursor solutions took on yellow. The precursor solution was spin-coated at 2000 rpm on FTO being accompanied by hydrolysis in an ambient atmosphere and by heat treatment at 150 °C for 1 h. A sol-gel anatase TiO₂ film was prepared by heating a TiO_x precursor coated FTO electrode at 450 °C for 30 min. A bulk-heterojunction active layer was prepared onto the as-prepared FTO/TiO_x or TiO₂ substrate by spin-coating at 700 rpm a mixed chlorobenzene solution containing 25 g $\rm L^{-1}$ P3HT and 20 g L⁻¹ PCBM. Further, a PEDOT:PSS aqueous dispersion solution was spin-coated at 6000 rpm onto its blend film. Finally, an Au metal as the back cathode was vacuum-deposited on the PEDOT:PSS solid film, the effective area of the solar cell being restricted to 1.0 cm² by a shadow mask. The device was heated at 150 °C for an annealing treatment. If necessary, the device was covered with a glass plate coated by an epoxy UV resin as sealing material in an N2 filled glove box. After charging a water getter sheet (Komatsu Seiren Co., Ltd.) into the slight space of about 40 µm thickness between the device surface and the glass plate, the sealing treatment was finally completed by irradiating UV light to the epoxy resin.

2.3. Measurement.

The X-ray diffraction (XRD) measurement was carried out using an X-ray diffractometer Rigaku RINT 2500 with Cu Kα radiation at 20 kV x 10 mA. A Hitachi S-4500 scanning electron microscopic (SEM) operated at an accelerating voltage of 15 kV was used in order to observe the surface morphology of the titanium oxide and estimate the thickness of each layer in the device. The photocurrent-voltage (I-V) curves of the solar cells were measured at 5 V min⁻¹ of a scan rate in linear sweep voltammetry (LSV) under a solar simulated light AM 1.5-100 mW cm⁻² by a Kansai Kagakukikai XES-502S solar simulator. Durability test of the solar cells was carried out by an interval LSV measurement in combination with a rest voltage measurement under continuous irradiation of the AM1.5-100 mW cm⁻² light. All the electric measurements were implemented in an ambient atmosphere using a Hokuto Denko HZ-5000 electrochemical analyzer. Ionization potentials for P3HT, PCBM, PEDOT:PSS, FTO, and Au were estimated by a Riken Keiki model AC-2, and band gap energies for P3HT and PCBM by a Hitachi U-3310 spectrophotometer.

3. Results and Discussion

The XRD pattern of the electrodeposited titanium oxide film on the FTO electrode after heating at 450 °C showed two peaks at $2\theta = 25.2^{\circ}$ and $2\theta = 48^{\circ}$ labeled orientation along the (101) and (200) planes, respectively. This TiO₂ was assigned to an anatase-type crystal structure. In contrast, the XRD pattern of the film after heating at 150 °C showed no peaks, indicating that the titanium oxide is an amorphous TiO_x. Surface SEM images of the TiO_x and TiO₂ films are shown in Figure 2. The SEM images showed that the both FTO substrates are densely covered with titanium oxide particles of ca. $20 \sim 50$ nm size. Cross sectional SEM images of the electrodeposited film and the sol-gel prepared film are shown in Figures 2(d) and (e). Although the electrodeposited film was more irregular than the sol-gel prepared film, thicknesses of both films were ca. 90-100 nm.

Figure 3 shows the photo I-V curves of the inverted type solar cells with and without titanium oxide layers. The performance of the cell without the layer showed the short-circuit photocurrent (J_{sc}) of 5.28 mA cm⁻², the open-circuit voltage (V_{oc}) of 0.32 V, the fill factor (FF) of 0.26, and the power conversion efficiency (η) of 0.45 %, see curve (a). Whereas, the performance of the cell with electrodeposited amorphous TiO_x layer showed $J_{sc} = 6.95$ mA cm⁻², V_{oc} = 0.55 V, FF = 0.56, and η = 2.13 %, see curve (b), the η value being 4.7 times higher than that without the TiO_x layer. This result implies that the rectification property of the device was improved because the TiO_x layer acted as both of electron-collecting and hole-blocking layers. That is, when the electrodeposited TiO_x layer covered almost completely on the FTO substrates, the recombination between the collected electrons into the n-type semiconductor TiO_x and the resided holes in P3HT:PCBM blend was remarkably suppressed. Additionally, the η value of the cell with the electrodeposited anatase TiO₂ layer increased up to 2.48 % by the improvement of J_{sc} (7.88 mA cm⁻²), see curve (c). This suggests that the carrier density and/or the electron mobility in the TiO₂ layer increased with a crystallization of the titanium oxide layer by the heat treatment. However, in the control experiment employing the TiO₂ layer prepared by sol-gel technique, the solar cell showed η of 1.99 %, see curve (d). This FTO surface has a texture structure to gain the photocurrent quantum yield by light scattering, being composed of mountains of about 200 nm height with the width of 100 ~ 300 nm as shown in Figure 2 (a). Therefore, the TiO₂ layer was partially very thin although it covered roughly on the FTO substrates by the sol-gel method, see Figure 2 (e). The recombination between the collected electrons in TiO2 and the resided holes in P3HT:PCBM blend may occur partly at the interface of the thin TiO₂ layer.

In the time course of the photo I-V curves of the solar cells with the electrodeposited TiO_x and TiO_2 films, when the anatase TiO_2 layer was inserted between the FTO substrate and the P3HT:PCBM organic layer, the η reached the maximum value within a few minutes

after light irradiation. In contrast, for the cell with the amorphous TiO_x , the improvement of the cell performance was observed very slowly with increasing the irradiation time. As a result, the maximum performance was obtained after irradiating for 90 min. The difference of its time dependence implies that the carrier density in the TiO_x is lower than that in the TiO_2 , reflecting that the J_{sc} value of the cell with TiO_2 was larger than that with TiO_x as shown in Figure 3.

The photo I-V of the FTO/electrodeposited amorphous curves TiO_x/P3HT:PCBM/PEDOT:PSS/Au FTO/electrodeposited and the anatase TiO₂/P3HT:PCBM/PEDOT:PSS/Au inverted type solar cells were measured with and without a UV light cut filter which takes off the light of less than 440 nm being slightly contained in AM1.5-100 mW cm^{-2} simulated sunlight, see Figure 4. For the TiO_x inserted cell, the photocurrent was not absolutely observed by the light irradiation with the filter, see curve (a). But the η of 2.13 % was obtained by the irradiation without the filter, see curve (c). On the other hand, when the anatase TiO_2 cell ($\eta = 2.48$ %) was covered by the filter, the performance decreased down to 0.39 %, see curve (b). The electrons produced in the TiO_x and TiO₂ bulk by irradiating UV light may fill firstly into electron traps of the titanium oxide interfering with the electron transport, and secondly after irradiating the UV light for a short period of time, they may transport relatively smooth because of the decrease of the trap sites.

The durability test was carried out in an ambient atmosphere. The comparison of the η against irradiation time for the inverted type organic solar cells with an amorphous TiO_x (open square) and an anatase TiO_2 (open circle) is shown in Figure 5. For the TiO_2 inserted type solar cell, the η decreased down to 80 % of the maximum value after light irradiation for 10 h, probably because of a photo-catalytic effect by anatase TiO_2 . In contrast, the η for the solar cell with the TiO_x layer was almost maintained under continuous light irradiation for 10 h. Furthermore, when this cell with the TiO_x layer was sealed using a glass plate, the

performance maintained 85 % of the maximum η value even after continuous light irradiation for 100 h. (Not shown) I believe that the stability of our cell is extremely high.

4. Conclusions

The present paper is report for the development and the performance evaluation of the inverted type organic solar cells inserting an electrodeposited titanium oxide layer between the FTO substrate and the P3HT:PCBM blend layer.

The η values of 2.1 and 2.5 % were obtained for the inverted type organic solar cells with the amorphous TiO_x and the anatase TiO₂, respectively. The TiO_x device without sealing exposed to air showed the high durability under continuous irradiation of AM 1.5-100 mW cm⁻² simulated sunlight for 10 h. In addition, this device with sealing maintained the relative efficiency over 85 % under continuous light irradiation for 100 h in air. These imply that the amorphous TiO_x and TiO₂ play an important role as both of the electron collection layer and the hole blocking layer, and inserting amorphous TiO_x is effective for preventing the performance degradation under continuous light irradiation. It will be possible to make more efficient and air-stable solar cells by controlling the surface morphology and the electric resistance of TiO_x and TiO₂.

Acknowledgements

This work was supported by the Incorporated Administrative Agency New Energy and Industrial Technology Development Organization (NEDO) under Ministry of Economy,

Trade and Industry (METI).

References

- [1] J.-i. Nakamura, C. Yokoe, K. Murata, K. Takahashi, J. Appl. Phys. 96 (2004) 6878-6883.
- [2] J.-i. Nakamura, S. Suzuki, K. Takahashi, C. Yokoe, K. Murata, Bull. Chem. Soc. Jpn. 77 (2004) 2185-2188.
- [3] K. Takahashi, T. Nishi, S. Suzaka, Y. Sigeyama, T. Yamaguchi, J.-i. Nakamura, K. Murata, Chem. Lett. 34 (2005) 768-769.
- [4] C. Waldauf, M. Morana, P. Denk, P. Schilinsky, K. Coakley, S. A. Choulis, C. J. Brabec, Appl. Phys. Lett. 89 (2006) 233517-1-3.
- [5] R. Steim, S. A. Choulis, P. Schilinsky, C. J. Brabec, Appl. Phys. Lett. 92 (2008) 093303-1-3.
- [6] G. K. Mor, K. Shankar, M. Paulose, O. K. Varghese, C. A. Grimes, Appl. Phys. Lett. 91 (2007) 152111-1-3.
- [7] K. Takahashi, K. Seto, T. Yamaguchi, J.-i. Nakamura, C. Yokoe, K. Murata, Chem. Lett. 33 (2004) 1042-1043.
- [8] K. Takahashi, T. Nakanishi, T. Yamaguchi, J.-i. Nakamura, K. Murata, Chem. Lett. 34 (2005) 714-715.
- [9] D. C. Olson, J. Piris, R. T. Collins, S. E. Shaheen, D. S. Ginley, Thin Solid Films 496 (2006) 26-29.
- [10] K. Takanezawa, K. Hirota, Q.-S. Wei, K. Tajima, K. Hashimoto, J. Phys. Chem. C 111 (2007) 7218-7223.
- [11] C. Natarajan, G. Nogami, Journal of The Electrochemical Society 143 (1996) 1547-1550.
- [12] S. Karuppuchamy, K. Nonomura, T. Yoshida, T. Sugiura, H. Minoura, Solid State Ionics 151 (2002) 19-27.

- [13] J. Y. Kim, S. H. Kim, H.-H. Lee, K. Lee, W. Ma, X. Gong, A. J. Heeger, Adv. Mater. 18 (2006) 572-576.
- [14] J. Y. Kim, K. Lee, N. E. Coates, D. Moses, T.-Q. Nguyen, M. Dante, A. J. Heeger, Science 317 (2007) 222-225.

Figure captions

Figure 1 Schematic structures of a normal (a) and an inverted type organic solar cells (b), and energy-level diagram (c) showing the work functions and the HOMO-LUMO energies of the component materials.

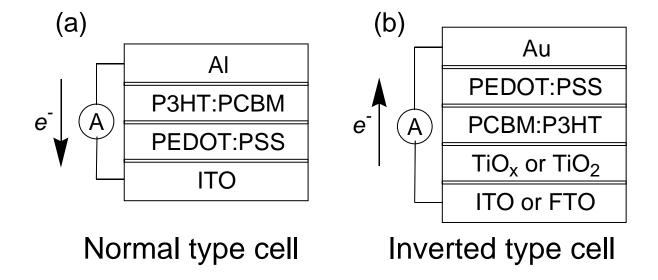
Figure 2 Surface SEM images of the bare FTO substrate (a), the as-synthesized TiO_x (b) and TiO_2 films (c) obtained from annealing the electrodeposited films at 150 °C and 450 °C, respectively. Cross sectional SEM images of the electrodeposited TiO_2 film (d) and the sol-gel prepared TiO_2 film (e) on the FTO substrates.

Figure 3 Photo I-V curves of the solar cells without the TiO_2 layer (a) and with the electrodeposited amorphous TiO_x layer (b), the electrodeposited anatase TiO_2 layer (c), and the TiO_2 layer prepared by a sol gel method (d), respectively.

Figure 4 Photo I-V curves of the FTO/amorphous $TiO_x/P3HT:PCBM/PEDOT:PSS/Au$ and FTO/anatase $TiO_2/P3HT:PCBM/PEDOT:PSS/Au$ type solar cells under light irradiation of AM 1.5-100 mW cm⁻² with and without UV light cut filter (< 440 nm).

Figure 5 Irradiation time dependences of the η for the inverted type organic solar cells with an amorphous TiO_x layer (open square) and an anatase TiO_2 layer (open circle).

The cells were exposed in air during the irradiation.



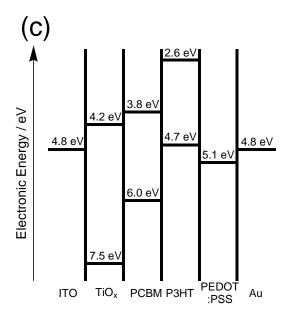


Figure 1

Kuwabara et al.

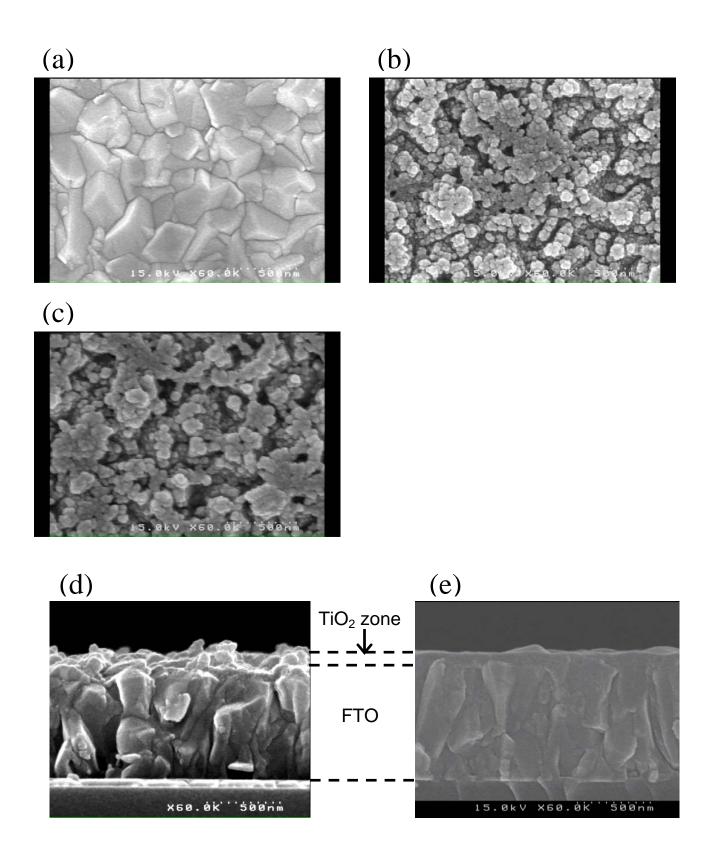


Figure 2

Kuwabara et al.

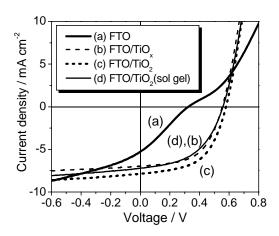


Figure 3

Kuwabara et al.

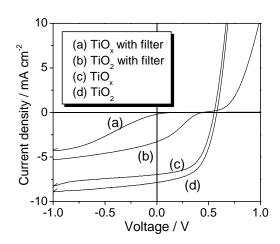


Figure 4

Kuwabara et al.

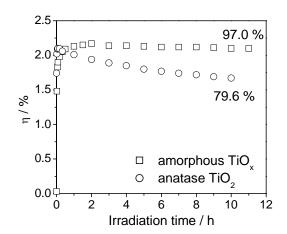


Figure 5

Kuwabara et al.